

Abstract of the Disclosure

A nonvolatile ferroelectric memory immediately outputs data stored in a page buffer without performing a
5 cell access operation when a page buffer is accessed. Since
a block page address region and a column page address
region are arranged in less significant bit region, and a
row address region is arranged in more significant bit
region, the cell operation is not performed in the access
10 of the page address buffer, thereby improving reliability
of the cell and reducing power consumption.